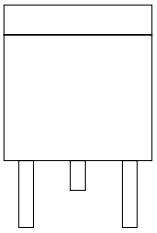
P-Channel Enhancement Mode MOSFET

Features

- -30V/-4A , $R_{DS(ON)}$<240mΩ(typ.) @ V_{GS}=-10V
  $R_{DS(ON)}$<460mΩ(typ.) @ V_{GS}=-4.5V
- Super High Dense Cell Design for Extremely Low $R_{DS(ON)}$
- Reliable and Rugged
- TO-252 Package

Pin Description

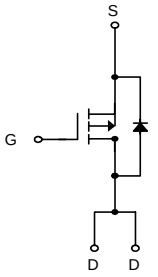


G D S

Top View of TO-252

Applications

- Power Management in Notebook Computer , Portable Equipment and Battery Powered Systems.



P-Channel MOSFET

Ordering and Marking Information

APM3195P □□-□□□

- Lead Free Code
- Handling Code
- Temp. Range
- Package Code

Package Code
U : TO-252
Operating Junction Temp. Range
C : -55 to 150°C
Handling Code
TU : Tube TR : Tape & Reel
Lead Free Code
L : Lead Free Device Blank : Original Device

APM3195P U :

XXXXX - Date Code

Absolute Maximum Ratings (T$_A$ = 25°C unless otherwise noted)

Symbol	Parameter	Rating	Unit
V_{DSS}	Drain-Source Voltage	-30	V
V_{GSS}	Gate-Source Voltage	±20	
I_D*	Maximum Drain Current – Continuous	- 4	A
I_{DM}	Maximum Drain Current – Pulsed	-16	

* Surface Mounted on FR4 Board, t ≤ 10 sec.

ANPEC reserves the right to make changes to improve reliability or manufacturability without notice, and advise customers to obtain the latest version of relevant information to verify before placing orders.

Rev. A.1 - Aug., 2002

Absolute Maximum Ratings Cont. (T_A = 25°C unless otherwise noted)

Symbol	Parameter		Rating	Unit
P_D	Maximum Power Dissipation	T_A=25°C	50	W
		T_A=100°C	20	
T_J	Maximum Junction Temperature		150	°C
T_{STG}	Storage Temperature Range		-55 to 150	°C
$R_{\theta JA}$*	Thermal Resistance – Junction to Ambient		50	°C/W

Electrical Characteristics (T_A = 25°C unless otherwise noted)

Symbol	Parameter	Test Condition	APM3195P			Unit
			Min.	Typ.	Max.	
Static						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_{DS}=-250µA	-30			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=-24V , V_{GS}=0V			-1	µA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS} , I_{DS}=-250µA	-1	-1.5	-2	V
I_{GSS}	Gate Leakage Current	V_{GS}=±20V , V_{DS}=0V			±100	nA
$R_{DS(ON)}$[a]	Drain-Source On-state Resistance	V_{GS}=-10V , I_{DS}=-4A			240	mΩ
		V_{GS}=-4.5V , I_{DS}=-3A			460	
V_{SD}[a]	Diode Forward Voltage	I_{SD}=-0.5A , V_{GS}=0V		-0.8	-1.3	V
Dynamic[b]						
Q_g	Total Gate Charge	V_{DS}=-15V , I_{DS}=-4A		8.1	10.5	nC
Q_{gs}	Gate-Source Charge	V_{GS}=-10V		2		
Q_{gd}	Gate-Drain Charge			1.1		
$t_{d(ON)}$	Turn-on Delay Time	V_{DD}=-15V , I_{DS}=-4A ,		10	20	ns
T_r	Turn-on Rise Time	V_{GEN}=-10V , R_G=6Ω		8	20	
$t_{d(OFF)}$	Turn-off Delay Time			25	50	
T_f	Turn-off Fall Time			5	15	
C_{iss}	Input Capacitance	V_{GS}=0V		507		pF
C_{oss}	Output Capacitance	V_{DS}=-25V		69		
C_{rss}	Reverse Transfer Capacitance	Frequency=1.0MHz		36		

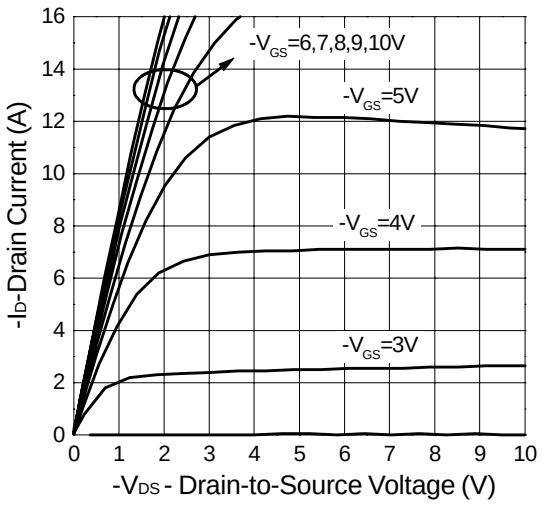
Notes

[a] : Pulse test ; pulse width ≤300µs, duty cycle ≤ 2%

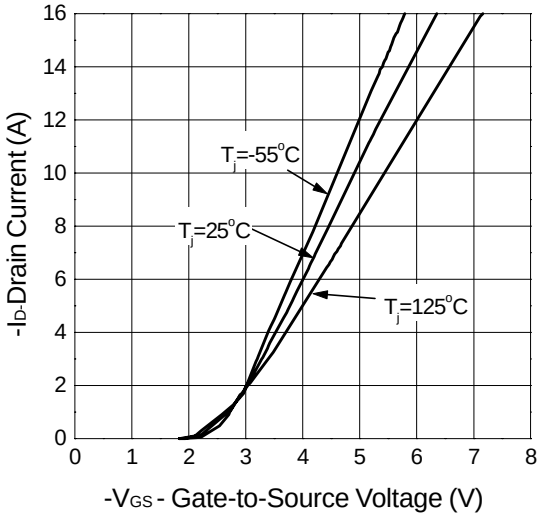
[b] : Guaranteed by design, not subject to production testing

Typical Characteristics

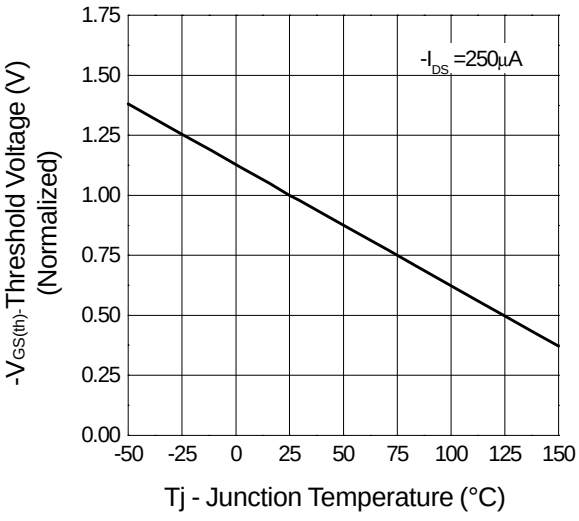
Output Characteristics



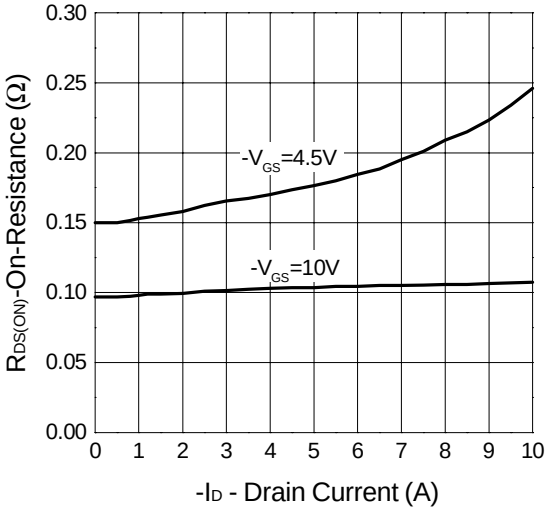
Transfer Characteristics



Threshold Voltage vs. Junction Temperature

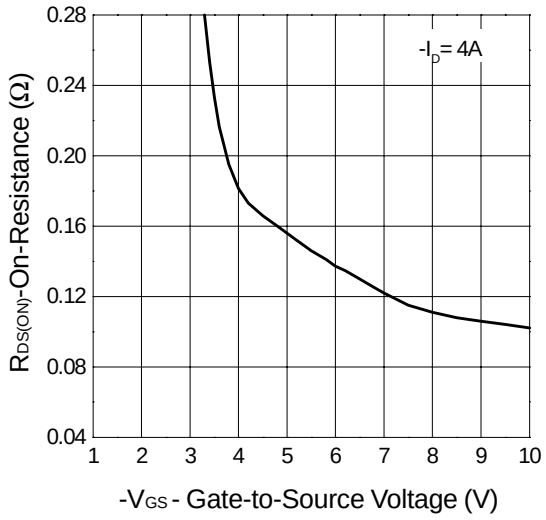


On-Resistance vs. Drain Current

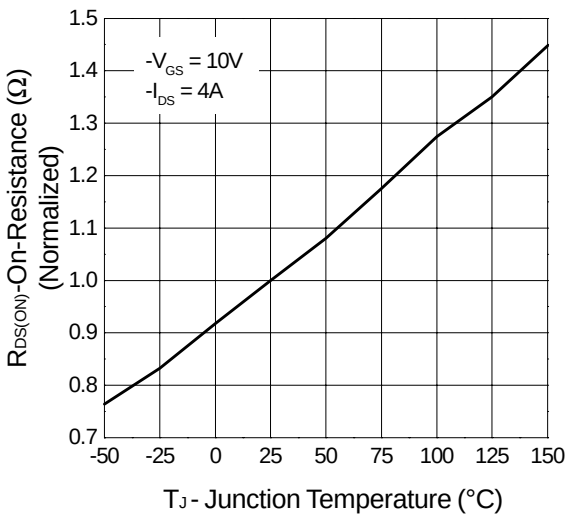


Typical Characteristics

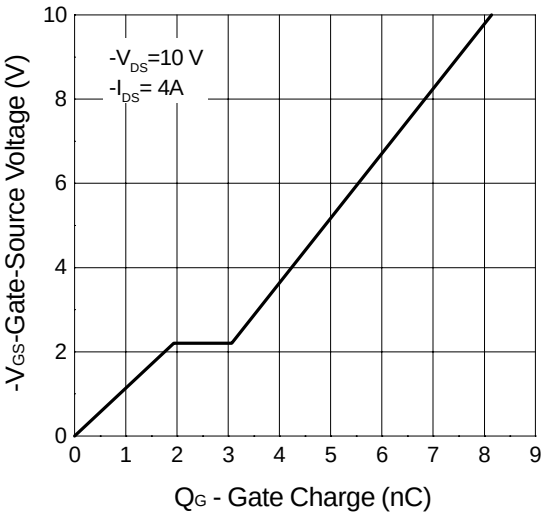
On-Resistance vs. Gate-to-Source Voltage



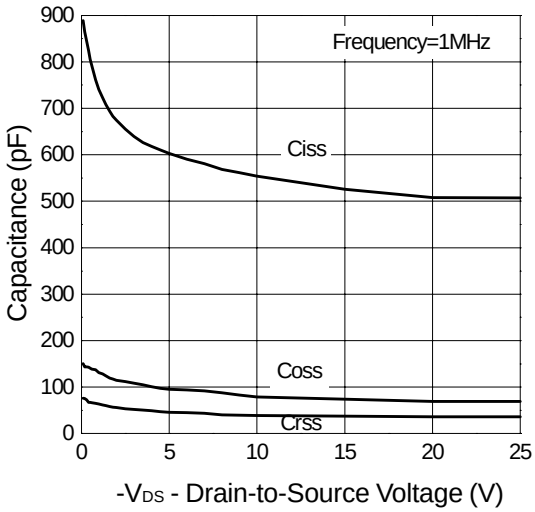
On-Resistance vs. Junction Temperature



Gate Charge

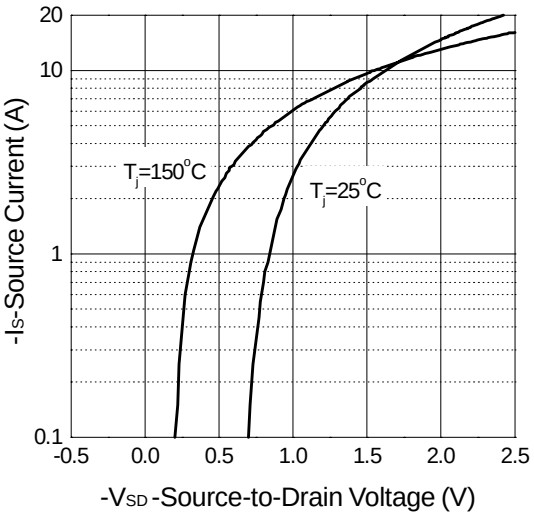


Capacitance

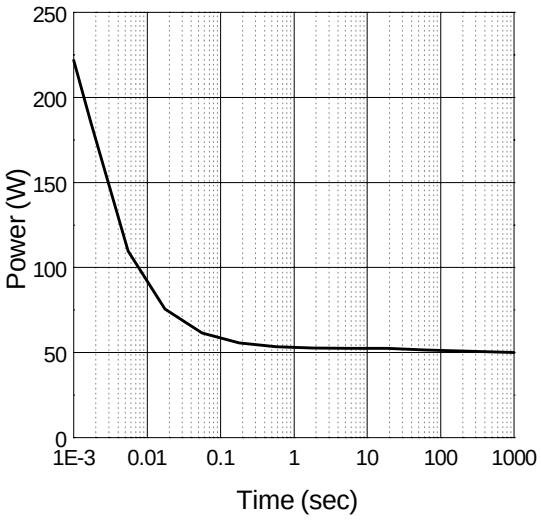


Typical Characteristics

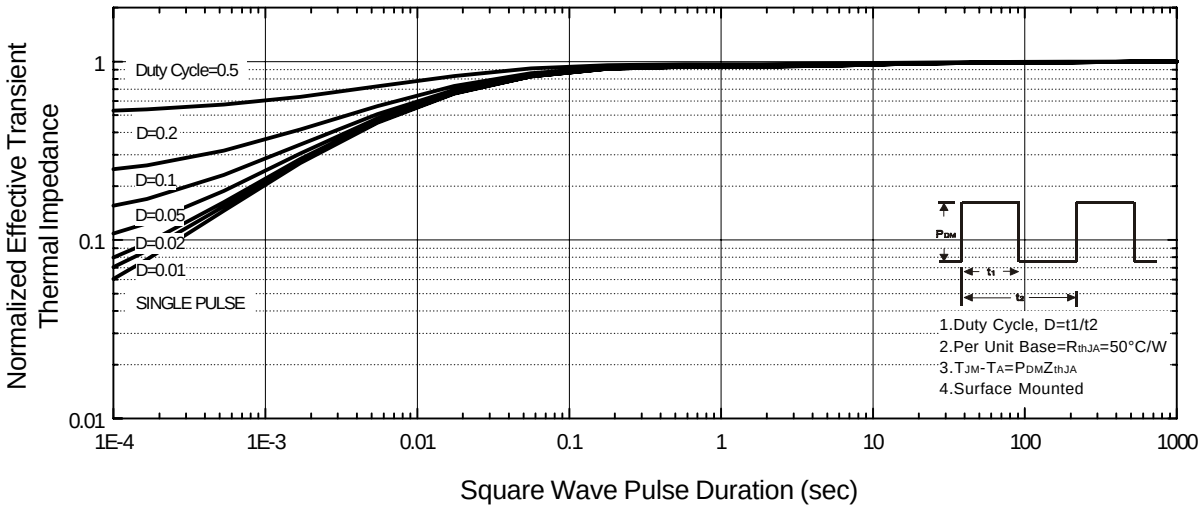
Source-Drain Diode Forward Voltage



Single Pulse Power

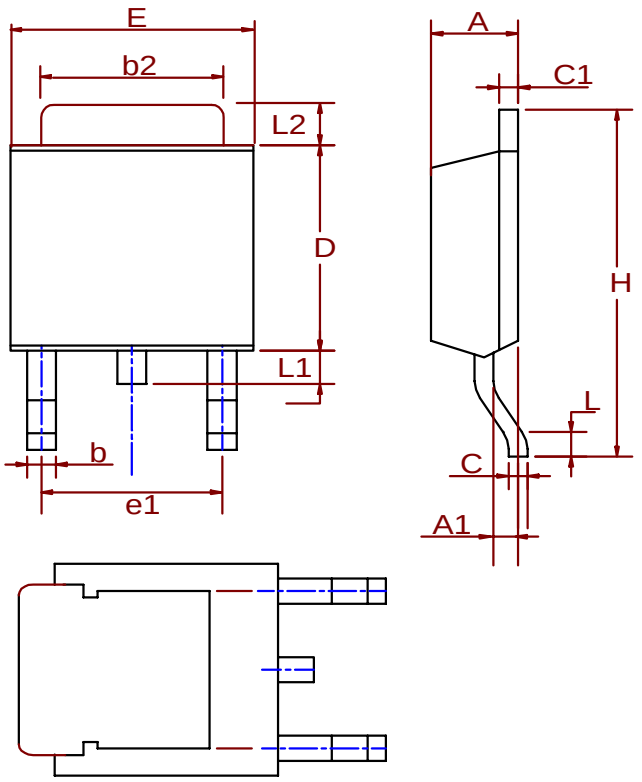


Normalized Thermal Transient Impedence, Junction to Ambient



Packaging Information

TO-252(Reference JEDEC Registration TO-252)

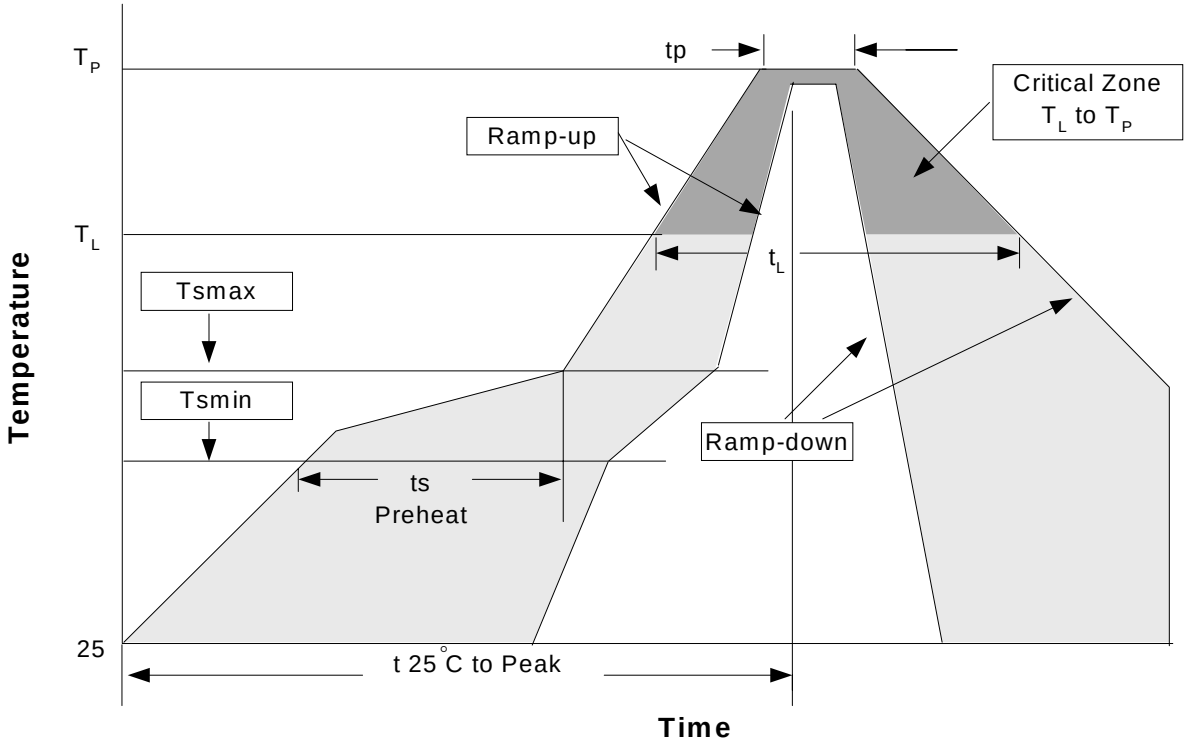


Dim	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	2.18	2.39	0.086	0.094
A1	0.89	1.27	0.035	0.050
b	0.508	0.89	0.020	0.035
b2	5.207	5.461	0.205	0.215
C	0.46	0.58	0.018	0.023
C1	0.46	0.58	0.018	0.023
D	5.334	6.22	0.210	0.245
E	6.35	6.73	0.250	0.265
e1	3.96	5.18	0.156	0.204
H	9.398	10.41	0.370	0.410
L	0.51		0.020	
L1	0.64	1.02	0.025	0.040
L2	0.89	2.032	0.035	0.080

Physical Specifications

Terminal Material	Solder-Plated Copper (Solder Material : 90/10 or 63/37 SnPb), 100%Sn
Lead Solderability	Meets EIA Specification RSI86-91, ANSI/J-STD-002 Category 3.

Reflow Condition (IR/Convection or VPR Reflow)



Classificatin Reflow Profiles

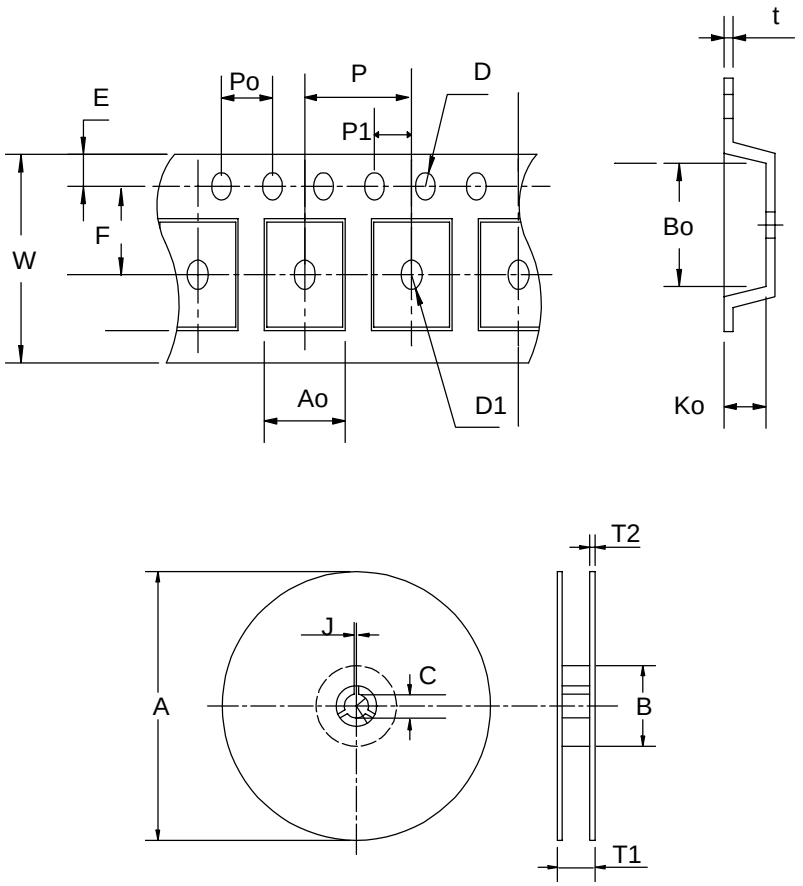
Profile Feature	Sn-Pb Eutectic Assembly		Pb-Free Assembly	
	Large Body	Small Body	Large Body	Small Body
Average ramp-up rate (T_L to T_P)	3°C/second max.		3°C/second max.	
Preheat - Temperature Min (Tsmin) - Temperature Mix (Tsmax) - Time (min to max)(ts)	100°C 150°C 60-120 seconds		150°C 200°C 60-180 seconds	
Tsmax to T_L - Ramp-up Rate			3°C/second max	
Tsmax to T_L - Temperature(T_L) - Time (t_L)	183°C 60-150 seconds		217°C 60-150 seconds	
Peak Temperature(Tp)	225 +0/-5°C	240 +0/-5°C	245 +0/-5°C	250 +0/-5°C
Time within 5°C of actual Peak Temperature(tp)	10-30 seconds	10-30 seconds	10-30 seconds	20-40 seconds
Ramp-down Rate	6°C/second max.		6°C/second max.	
Time 25°C to Peak Temperature	6 minutes max.		8 minutes max.	

Note: All temperatures refer to topside of the package. Measured on the body surface.

Reliability Test Program

Test item	Method	Description
SOLDERABILITY	MIL-STD-883D-2003	245°C,5 SEC
HOLT	MIL-STD 883D-1005.7	1000 Hrs Bias @ 125°C
PCT	JESD-22-B, A102	168 Hrs, 100% RH, 121°C
TST	MIL-STD 883D-1011.9	-65°C ~ 150°C, 200 Cycles

Carrier Tape & Reel Dimensions



Application	A	B	C	J	T1	T2	W	P	E
TO-252	330 ±3	100 ± 2	13 ± 0. 5	2 ± 0.5	16.4 + 0.3 -0.2	2.5± 0.5	16+ 0.3 - 0.1	8 ± 0.1	1.75± 0.1
	F	D	D1	Po	P1	Ao	Bo	Ko	t
	7.5 ± 0.1	1.5 +0.1	1.5± 0.25	4.0 ± 0.1	2.0 ± 0.1	6.8 ± 0.1	10.4± 0.1	2.5± 0.1	0.3±0.05

(mm)

Cover Tape Dimensions

Application	Carrier Width	Cover Tape Width	Devices Per Reel
TO- 252	16	13.3	2500

Customer Service

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